## PNP Silicon Epitaxial Transistors

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT–223 package which is designed for medium power surface mount applications.

- High Current
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow.
   The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Device Marking:

BCP53T1G = AH

BCP53-10T1G = AH-10

BCP53-16T1G = AH-16

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-100	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current	I <sub>C</sub>	1.5	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

## THERMAL CHARACTERISTICS

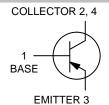
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath	T <sub>L</sub>	260 10	° °



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## MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



## **MARKING DIAGRAM**



SOT-223 CASE 318E STYLE 1



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code • Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
BCP53T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
BCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
BCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
SBCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel	
BCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel	
NSVBCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel	
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<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Breakdown Voltage $(I_C = -100 \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	-100	_	-	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-80	-	-	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = -100 \mu Adc, R_{BE} = 1.0 k\Omega$ )	V <sub>(BR)CER</sub>	-100	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	-5.0	-	-	Vdc
Collector-Base Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	_	_	-100	nAdc
Emitter–Base Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	-	-100	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = -5.0 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ &\text{All Part Types} \\ &(I_C = -150 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ &\text{BCP53, SBCP53} \\ &\text{BCP53-10, SBCP53-10} \\ &\text{BCP53-16, SBCP53-16, NSVBCP53-16} \\ &(I_C = -500 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ &\text{All Part Types} \end{aligned} $	h <sub>FE</sub>	25 40 63 100 25	- - - -	- 250 160 250	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>CE(sat)</sub>	_	-	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc)	V <sub>BE(on)</sub>	_	-	-1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product ( $I_C = -10 \text{ mAdc}$ , $V_{CE} = -5.0 \text{ Vdc}$ , $f = 35 \text{ MHz}$ )	f <sub>T</sub>	_	50	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **TYPICAL CHARACTERISTICS**

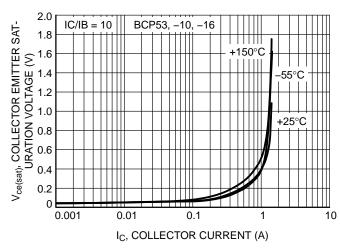


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

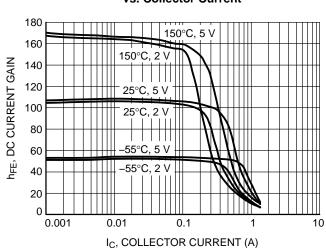


Figure 3. DC Current Gain vs. Collector Current (BCP53-10)

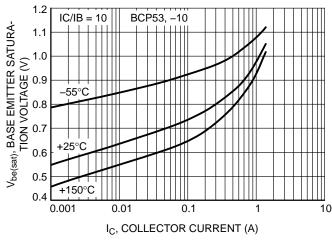


Figure 5. BCP53, –10 Base Emitter Saturation Voltage vs. Collector Current

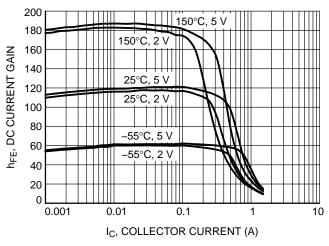


Figure 2. DC Current Gain vs. Collector Current (BCP53)

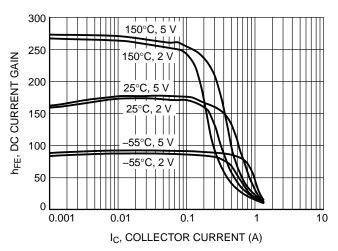


Figure 4. DC Current Gain vs. Collector Current (BCP53-16)

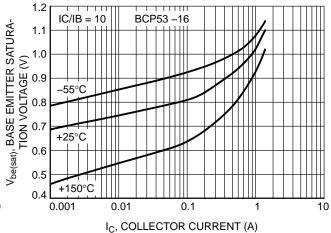
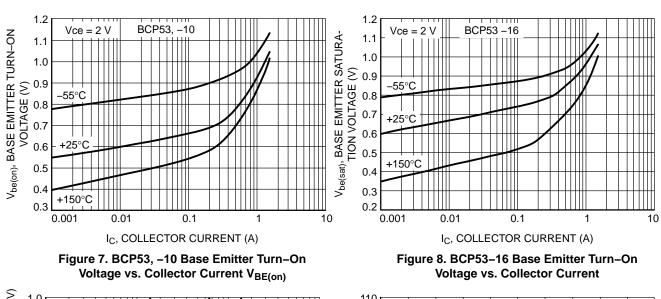


Figure 6. BCP53-16 Base Emitter Saturation Voltage vs. Collector Current

## **TYPICAL CHARACTERISTICS**



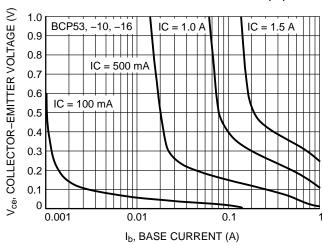


Figure 9. BCP53, -10, -16 Saturation Region

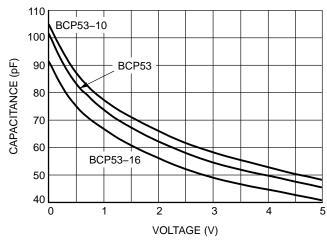


Figure 10. Input Capacitance

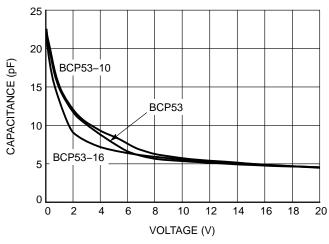


Figure 11. Output Capacitance

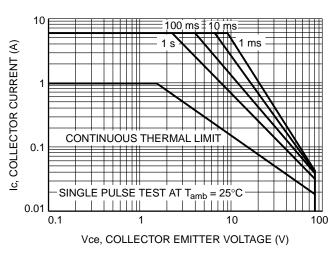
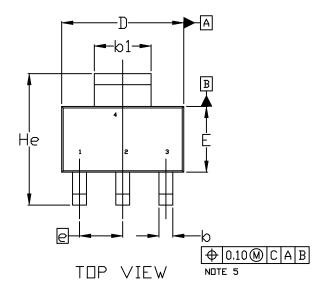


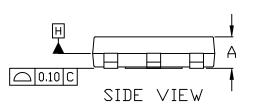
Figure 12. Standard Operating Area

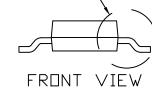


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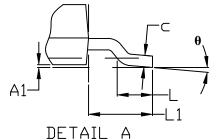
**DATE 02 OCT 2018** 







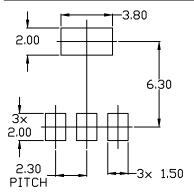
SEE DETAIL A



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
Ø	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
U	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10°	



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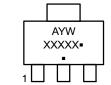
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**DATE 02 OCT 2018** 

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

# GENERIC MARKING DIAGRAM\*



A = Assembly Location

Y = Year W = Work Week

 $XXXXX \ = Specific \ Device \ Code$ 

= Pb-Free Package

(Note: Microdot may be in either location)
\*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may
not follow the Generic Marking.

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